

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
100V	15mΩ @ V _{GS} = 10V	52.5A
	18mΩ @ V _{GS} = 6.0V	49.5A
	25mΩ @ V _{GS} = 4.5V	40.8A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

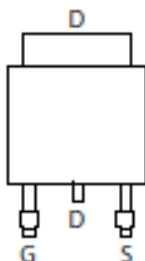
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_G – Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**
- An Automotive-Compliant Part is Available Under Separate Datasheet ([DMTH10H015LK3Q](#))**

Mechanical Data

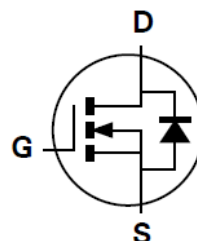
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208
- Weight: 0.33grams (Approximate)



Top View



Pin Out Top View



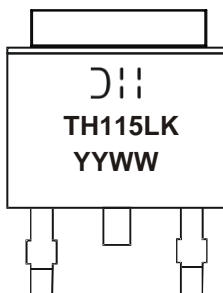
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H015LK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
- EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



= Manufacturer's Marking
 TH115LK = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 17 = 2017)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V	I _D	52.5 37.1	A
		T _C = +25°C T _C = +100°C	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	150	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	150	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	2.6	A
Avalanche Current, L = 3mH	I _{AS}	7.5	A
Avalanche Energy, L = 3mH	E _{AS}	85	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	69	°C/W
Total Power Dissipation (Note 6)	P _D	3.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	42	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.4	—	3.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	10.7	15	mΩ	V _{GS} = 10V, I _D = 20A
		—	13.1	18		V _{GS} = 6V, I _D = 20A
		—	18.2	25		V _{GS} = 4.5V, I _D = 5A
		—	—	—		V _{GS} = 0V, I _S = 20A
Diode Forward Voltage	V _{SD}	—	—	1.3	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	1,871	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	261	—		
Reverse Transfer Capacitance	C _{RSS}	—	6.9	—		
Gate Resistance	R _G	—	1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _G	—	33.3	—	nC	V _{DD} = 50V, I _D = 10A, V _{GS} = 10V
Gate-Source Charge	Q _{GS}	—	6.9	—		
Gate-Drain Charge	Q _{GD}	—	5.1	—		
Turn-On Delay Time	t _{D(ON)}	—	6.5	—	ns	V _{DD} = 50V, V _{GS} = 10V, I _D = 10A, R _G = 6Ω
Turn-On Rise Time	t _R	—	7.0	—		
Turn-Off Delay Time	t _{D(OFF)}	—	19.7	—		
Turn-Off Fall Time	t _F	—	8.1	—		
Reverse Recovery Time	t _{RR}	—	37.9	—	ns	I _F = 10A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	51.9	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

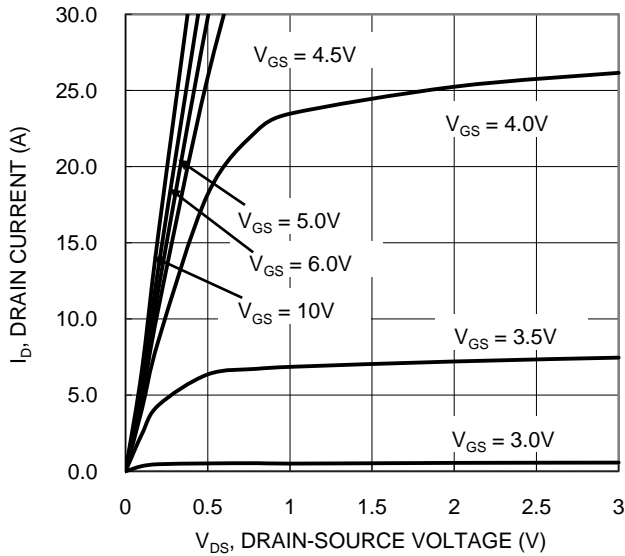


Figure 1. Typical Output Characteristic

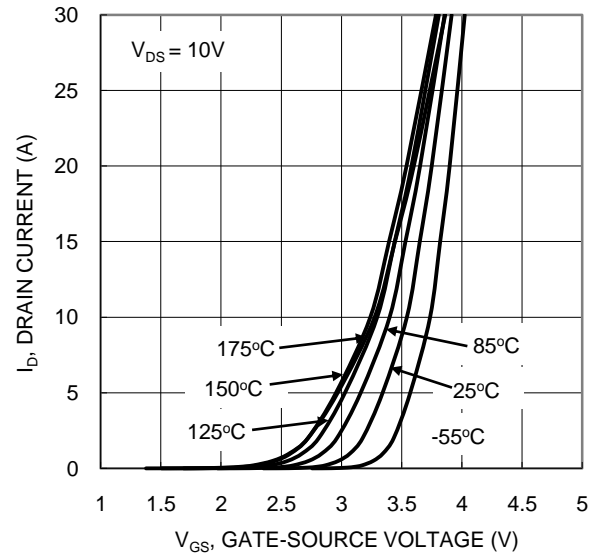


Figure 2. Typical Transfer Characteristic

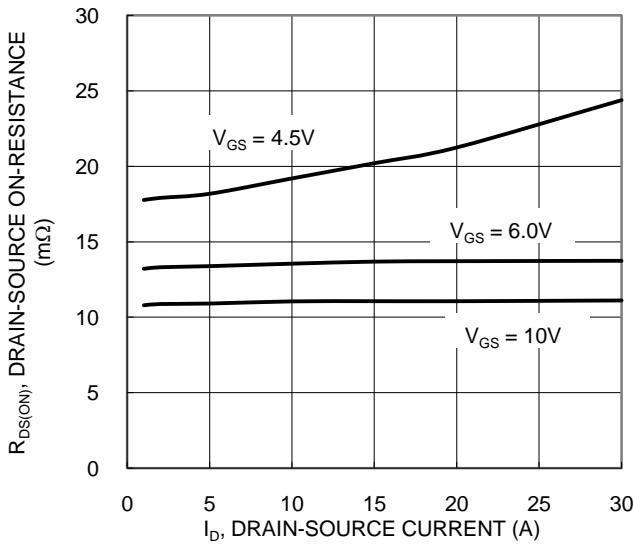


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

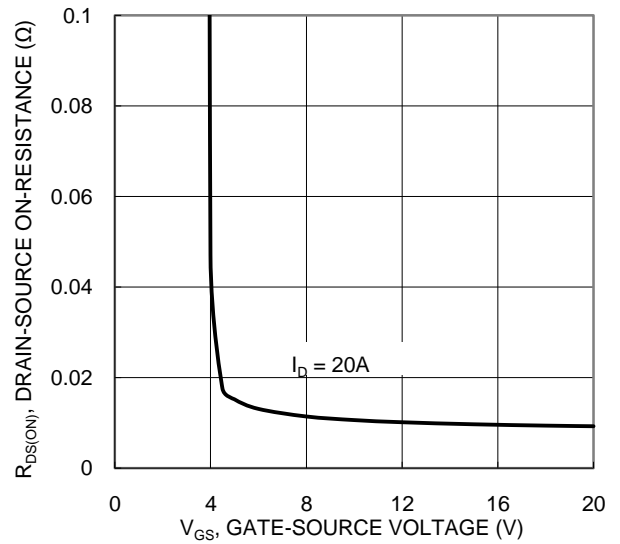


Figure 4. Typical Transfer Characteristic

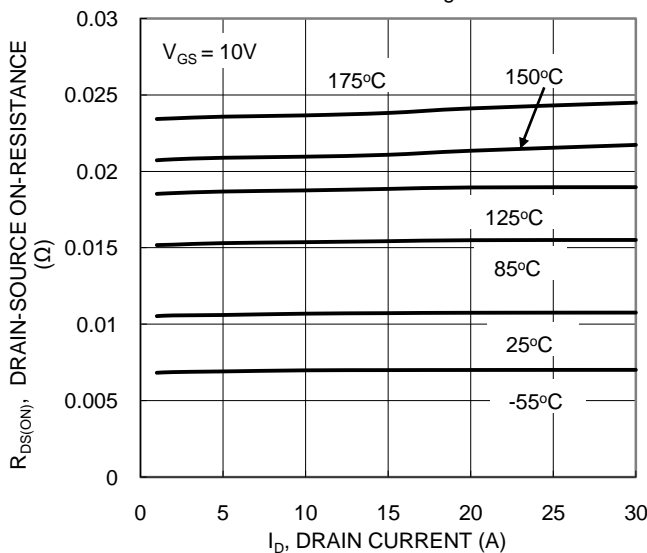


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

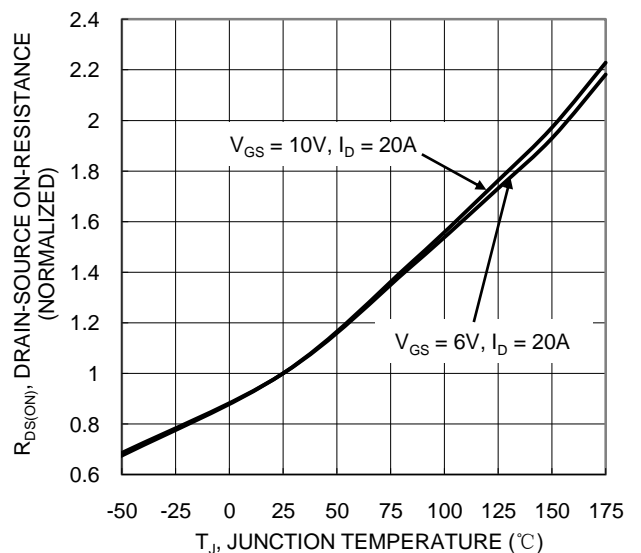


Figure 5. On-Resistance Variation with Junction Temperature

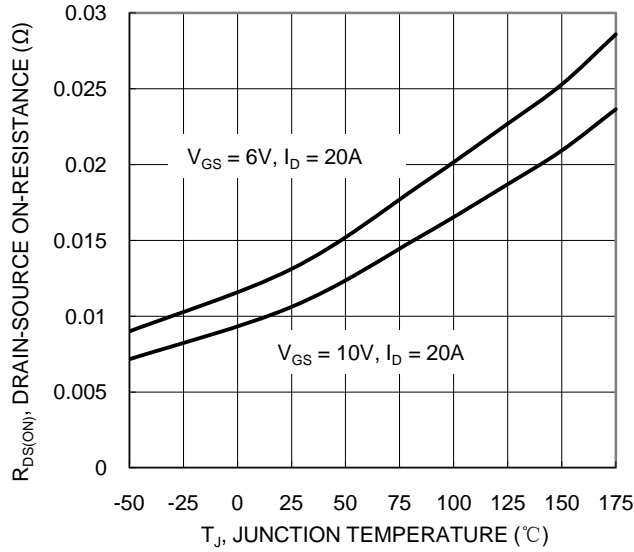


Figure 7. On-Resistance Variation with Junction Temperature

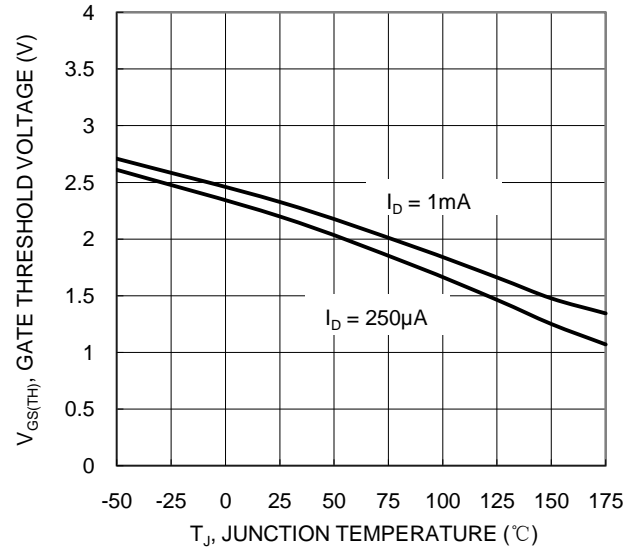


Figure 8. Gate Threshold Variation vs. Junction Temperature

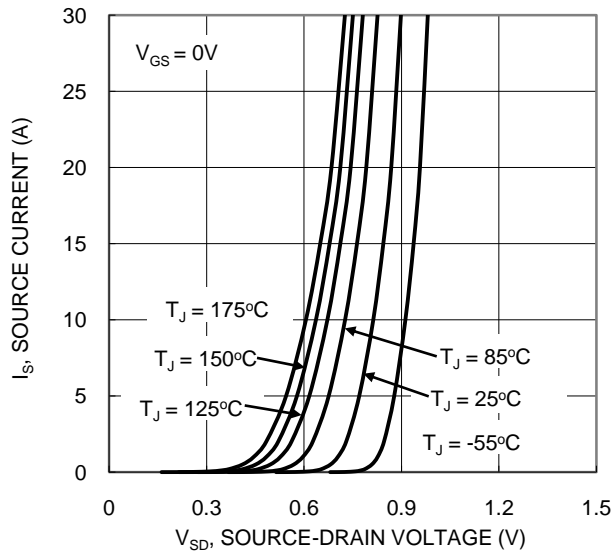


Figure 9. Diode Forward Voltage vs. Current

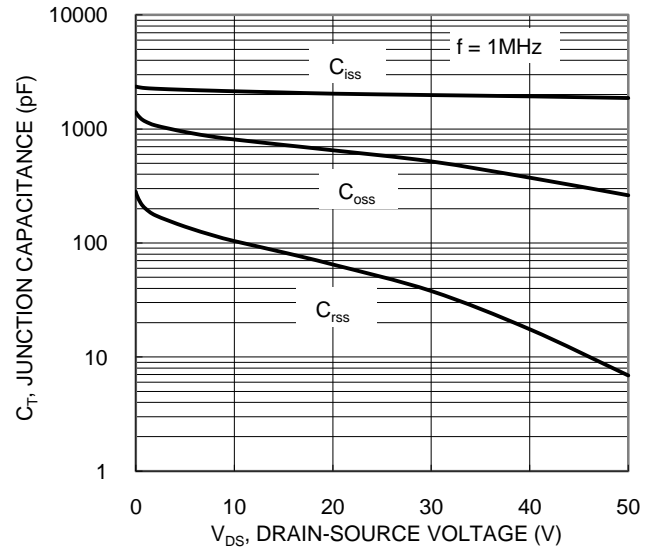


Figure 10. Typical Junction Capacitance

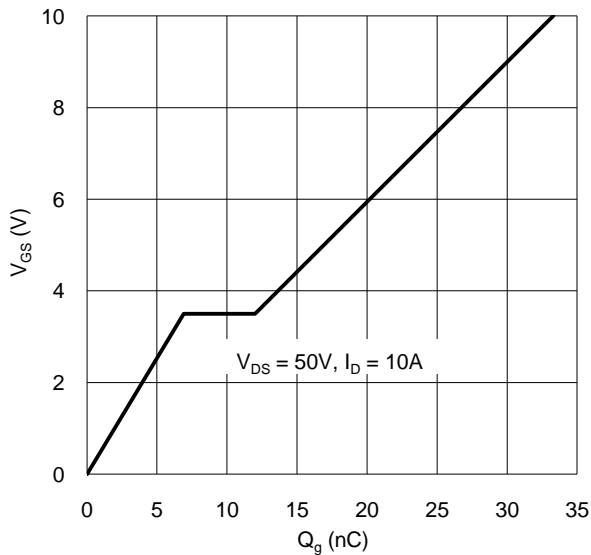


Figure 11. Gate Charge

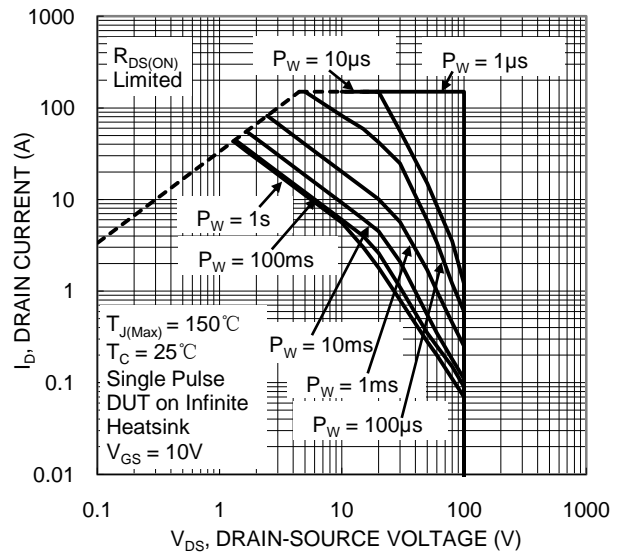


Figure 12. SOA, Safe Operation Area

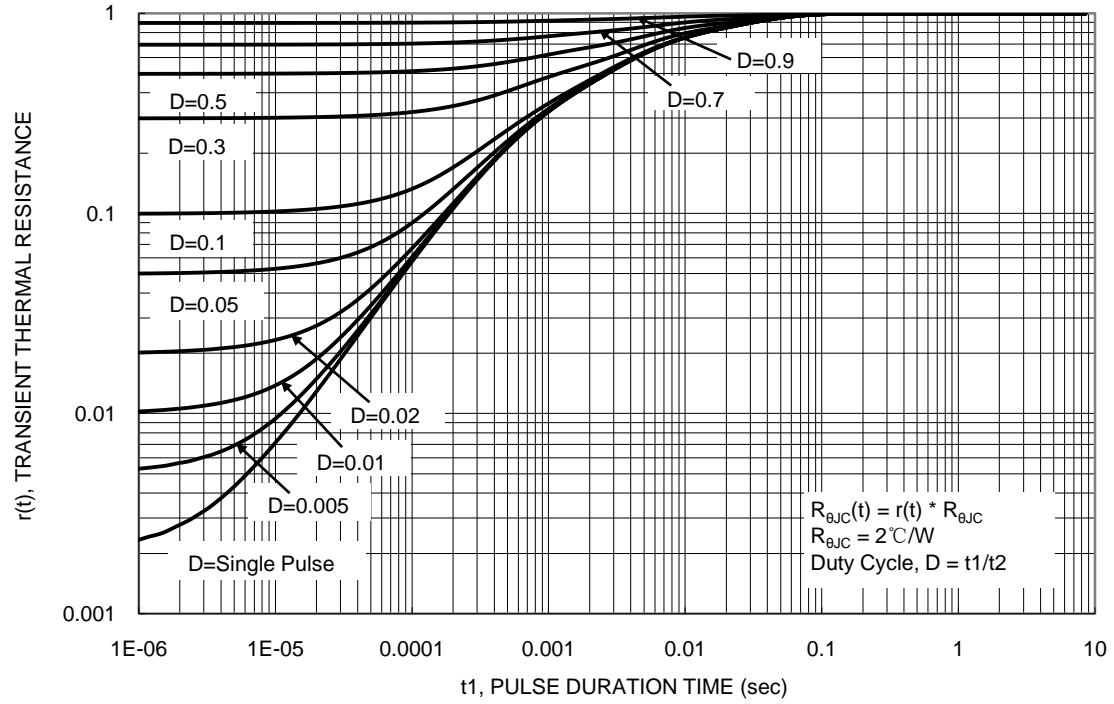
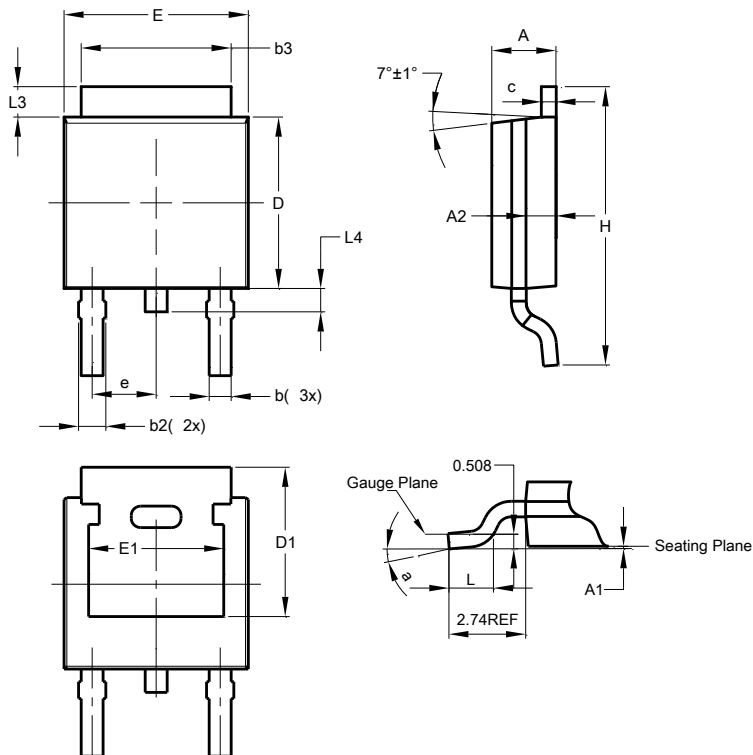


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

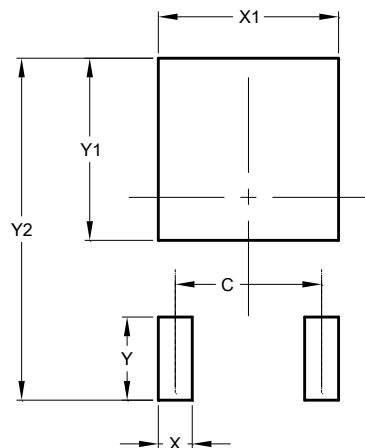


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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